ABSTRACT

Disclosed is a method for forming conducting wire and contact opening in a semiconductor device. The method comprises steps of providing a substrate; forming a first dielectric layer on the substrate; digging a via in the first dielectric layer and filling metal therein; forming a conductor layer on the first dielectric including the via; forming a metal layer on the conductor layer; removing unnecessary portions of the conductor/metal layers to define recesses, with the left portions to form conducting wires; applying a second dielectric layer to fill the recesses and performing planarization thereto to expose the conducting wires; forming a third dielectric layer; forming photoresist of predetermined pattern on the third dielectric layer; removing predetermined portion of the third dielectric layer to form a contact opening; and removing the photoresist.